Transistors

# 4V Drive Pch MOS FET RSM002P03

## Structure

Silicon P-channel MOS FET

## Features

- 1) Low On-resistance.
- 2) Small package (VMT3).
- 3) 4V drive.

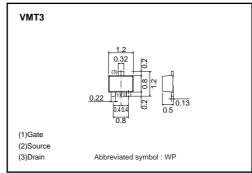
## Applications

Switching

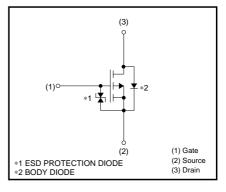
#### Packaging specifications

	Package	Taping	
Туре	Code	T2L	
	Basic ordering unit (pieces)	8000	
RSM002P03		0	

## •External dimensions (Unit : mm)



#### Inner circuit



#### •Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	-30	V	
Gate-source voltage		Vgss	±20	V	
Drain ourrent	Continuous	ID	±0.2	А	
Drain current	Pulsed	I <sub>DP</sub> *1	±0.4	А	
Total power dissipation		P <sub>D</sub> *2	0.15	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

\*1 Pw≤10µs, Duty cycle≤1%

\*2 Each terminal mounted on a recommended land

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	833	°C/W

\* Each terminal mounted on a recommended land

# Transistors

# •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	±10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Drain-source breakdown voltage	V(BR) DSS	-30	-	_	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V	
Zero gate voltage drain current	IDSS	-	-	-1	μA	$V_{DS}$ = -30V, $V_{GS}$ =0V	
Gate threshold voltage	VGS (th)	-1.0	-	-2.5	V	$V_{DS} = -10V, I_{D} = -1mA$	
Static drain-source on-state resistance	R <sub>DS</sub> (on) <sup>*</sup>	-	0.9	1.4	Ω	I <sub>D</sub> = -0.2A, V <sub>GS</sub> = -10V	
		-	1.4	2.1	Ω	I <sub>D</sub> = -0.15A, V <sub>GS</sub> = -4.5V	
		-	1.6	2.4	Ω	I <sub>D</sub> = -0.15A, V <sub>GS</sub> = -4.0V	
Forward transfer admittance	Y <sub>fs</sub> *	0.2	-	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.15A	
Input capacitance	Ciss	-	30	-	pF	VDS=-10V	
Output capacitance	Coss	-	4	_	pF	V <sub>G</sub> s= 0V	
Reverse transfer capacitance	Crss	-	5	_	pF	f=1MHz	
Turn-on delay time	t <sub>d (on)</sub> *	_	8	_	ns	Vdd≒–15V	
Rise time	tr *	_	5	_	ns	ID= -0.15A	
Turn-off delay time	t <sub>d (off)</sub> *	_	30	_	ns	VGs= –10V R∟= 100Ω	
Fall time	t <sub>f</sub> *	-	40	_	ns	$R_{G}=10\Omega$	

\*Pulsed

# •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	-1.2	V	Is= -0.1A, V <sub>GS</sub> =0V

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